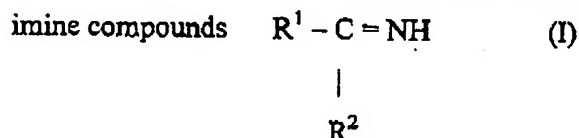


In the Claims:

1. (Currently amended) A polishing fluid useful for polishing tantalum-containing barrier materials of a semiconductor substrate, the semiconductor having a copper or copper alloy interconnect, comprising, by weight percent:

0.1 to 10a nitrogen-containing compound having at least two nitrogen atoms comprising at least one of a compound of a formula selected from the group comprising:



and hydrazine compounds $\text{R}^3\text{R}^4\text{N} - \text{NR}^5\text{R}^6$ (II),

wherein ~~R⁴ comprises H or NH₂ and R², R³, R⁴, R⁵ and R⁶ independently comprise substituents selected from the group consisting of -H, a hydrocarbon group, an amino group, a carbonyl group, an imido group, an azo group, a cyano group, a thio group, a seleno group and -OR⁷ where R⁷ comprises a hydrocarbon group, and the nitrogen-containing compound being free of electron-withdrawing substituents~~ and the imine compound includes either guanidine or formamidine; and

0.0025 to 2 benzotriazole; and

the polishing fluid having a pH of 8 to 11, containing no abrasive particles and being capable of removing the tantalum-containing barrier materials from a surface of the semiconductor substrate.

2. Cancelled.

3. (Original) The polishing fluid of claim 1, wherein the nitrogen-containing compound contains the imine compound.

4. (Original) The polishing fluid of claim 1, wherein the nitrogen-containing compound contains the hydrazine compound.

5. (Currently amended) A polishing fluid useful for polishing tantalum-containing barrier materials of a semiconductor substrate, the semiconductor having a copper or copper alloy interconnect, comprising, by weight percent:

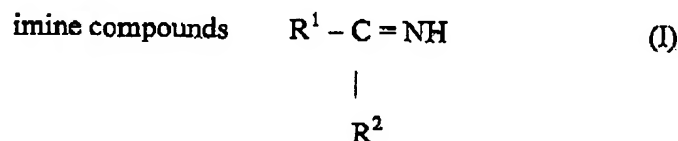
0.0025 to 2 benzotriazole ~~0 to 6 inhibitor~~ for reducing the removal of ~~an the copper or copper alloy interconnect metal~~;

~~0 to 1 weight percent abrasive particles~~;

0 to 25 oxidizing agent;

0 to 15 complexing agent and

0.05 to 25-0.1 to 10 nitrogen-containing compound having at least two nitrogen atoms comprising at least one of a compound of a formula selected from the group comprising:



and hydrazine compounds $R^3R^4N - NR^5R^6 \quad (II);$

wherein ~~R¹ comprises H or NH₂ and R², R³, R⁴, R⁵ and R⁶ independently comprise substituents selected from the group consisting of -H, a hydrocarbon group, an amino group, a carbonyl group, an imido group, an azo group, a cyano group, a thio group, a seleno group and -OR⁷ where R⁷ comprises a hydrocarbon group, and the nitrogen-containing compound having an electron-donating substituent, and the imine compound includes either guanidine or formamidine~~; and the polishing fluid having a pH of 8 to 11, containing no abrasive particles and being capable of removing the tantalum-containing barrier materials from a surface of the semiconductor substrate.

6. Cancelled.

7. (Original) The polishing fluid of claim 5, wherein the nitrogen-containing compound contains the imine compound and the imine compound contains at least one selected from at least one of the group comprising 1,3-diphenyl guanidine, guanidine hydrochloride, tetramethylguanidine, formamidine acetate and acetamidine hydrochloride.

8. (Previously presented) The polishing fluid of claim 5, wherein the nitrogen-containing compound contains the hydrazine compound and the hydrazine compound contains at least one selected from at least one of the group comprising carbohydrazide, acetic hydrazide, semicarbazide hydrochloride, and formic hydrazide.

9 and 10 Cancelled.